

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L22	1	(transistor and substrate and lateral and source and drain and conductivity and relaxation).clm.	US-PGPU B	OR	ON	2006/02/01 07:32

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L21	178	(transistor and substrate and lateral and source and drain and conductivity).clm.	US-PGPU B	OR	ON	2006/02/01 07:32
L22	1	(transistor and substrate and lateral and source and drain and conductivity and relaxation).clm.	US-PGPU B	OR	ON	2006/02/01 07:32
S60	61	(transistor with punch adj through near4 layer) with gate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/31 18:25
S61	10	(transistor with punch adj through near4 layer) with gate with stopper	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/31 18:29
S62	1066	(transistor with punch adj through near4 layer stopper near3 layer) with gate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/31 18:32
S63	916	S62 and (source drain)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/31 18:48
S64	24	S63 and relax\$5.near3 layer	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/02/01 07:25